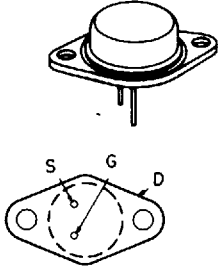



Power MOSFETS

| ECG Type | Description and Application | Transconductance gfs mhos | Drain to Source Breakdown Voltage BV _{DSS} | Gate to Source Breakdown Voltage BV _{GS} | Continuous Drain Current I _D Amps | Gate to Source Cutoff Voltage V _{GS} (off) | Drain to Source Resistance ^r DS (on) Ohms | Input Cap C _{iss} pf | Device Dissipation @T _C = 25°C PD Watts | Package | |
|------------------------------------|---|---------------------------|---|---|--|---|--|-------------------------------|--|--------------------|---|
| | | | | | | | | | | Case/ Fig./ Basing | |
| ECG2392 ▲ | MOSFET, N-Ch, Enhancement Hi Speed Switch | 6 Min | 100 Min | ± 20 Max* | 32 | 4 Max | .06 Max | 1500 Typ | 125 Max | TO-3 Fig. T28 |  |
| | | | | | | | | | | | |
| ECG2386 ▲ | MOSFET, N-Ch, Enhancement Hi Speed Switch | 2 Min | 600 Min | ± 20 Max* | 6 | 4.5 Max | 1.2 Max | 1800 Max | 150 Max | | |
| | | | | | | | | | | | |
| ECG2384 ▲ | MOSFET, N-Ch, Enhancement Hi Speed Switch | 1.8 Min | 800 Min | ± 20 Max* | 6 | 4 Max | 1.5 Max | 3500 Max | 125 Max | | |
| | | | | | | | | | | | |
| ECG2390 ▲ | MOSFET, N-Ch, Enhancement Hi Speed Switch | 3 Min | 60 Min | ± 20 Max* | 12 | 4.5 Max | .2 Max | 800 Max | 75 Max | TO-220 Fig. T41 |  |
| | | | | | | | | | | | |
| ECG2382 ▲ (Compl to ECG2383) | MOSFET, N-Ch, Enhancement Hi Speed Switch | 1.5 Min | 100 Min | ± 20 Max* | 8 | 4 Max | .5 Max | 750 Max | 75 Max | | |
| | | | | | | | | | | | |
| ECG2383 ▲ (Compl to ECG2382) | MOSFET, P-Ch, Enhancement Hi Speed Switch | 2 Min | 100 Min | ± 20 Max* | 8 | 4.5 Max | .4 Max | 1200 Max | 75 Max | | |
| | | | | | | | | | | | |
| ECG66 ▲ | MOSFET, N-Ch, Enhancement Hi Speed Switch | 3 Min | 100 Min | ± 20 Max* | 12 | 4.5 Max | .18 Max | 1200 Max | 75 Max | | |
| | | | | | | | | | | | |
| ECG2388 ▲ | MOSFET, N-Ch, Enhancement Hi Speed Switch | 5 Min | 200 Min | ± 20 Max* | 12.5 | 4 Max | .2 Max | 1000 Typ | 75 Max | | |
| | | | | | | | | | | | |
| ECG67 ▲ | MOSFET, N-Ch, Enhancement Hi Speed Switch | 2 Min | 400 Min | ± 20 Max* | 5 | 4.5 Max | 1.5 Max | 1200 Max | 75 Max | | |
| | | | | | | | | | | | |
| ECG2380 ▲ (Compl to ECG2381) | MOSFET, N-Ch, Enhancement Hi Speed Switch | 1 Min | 500 Min | ± 20 Max* | 2 | 4.5 Max | 4 Max | 500 Max | 75 Max | | |
| | | | | | | | | | | | |
| ECG2381 ▲ (Compl to ECG2380) | MOSFET, P-Ch, Enhancement Hi Speed Switch | .5 Min | 500 Min | ± 20 Max* | 2 | 4.5 Max | 6 Max | 1000 Max | 75 Max | | |
| | | | | | | | | | | | |
| ECG2385 ▲ | MOSFET, N-Ch, Enhancement Hi Speed Switch | 5 Min | 500 Min | ± 30 Max* | 8 | 4 Max | .8 Max | 1800 Max | 125 Max | | |
| | | | | | | | | | | | |
| ECG2387 ▲ | MOSFET, N-Ch, Enhancement Hi Speed Switch | 3 Min | 800 Min | ± 30 Max* | 4 | 4 Max | 3 Max | 1250 Max | 125 Max | | |
| | | | | | | | | | | | |

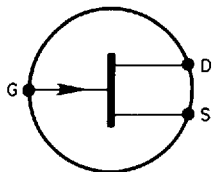
* Warning - Exceeding BV_{GS} maximum will result in permanent damage to the gate region oxide layer.

▲ Refer to MOSFET Handling Precautions - Page 1-31

Package Outline - See Page 1-76

FET and MOSFET Diagrams (Observe MOS Handling) ▲

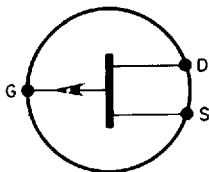
Depletion N-Ch JFET



ECG

312 456
451 457 461 (Dual) 468
452 458 466 469
453 459 467

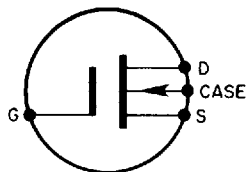
Depletion P-Ch JFET



ECG

326
460
489

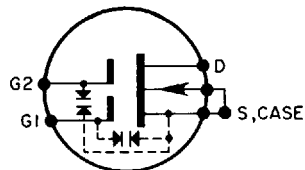
Depletion N-Ch MOSFET



ECG

220
462

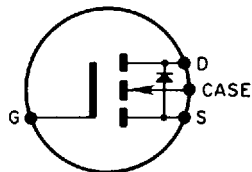
Dual Gate Depletion N-Ch MOSFET



ECG

221
222 (Gate Protected)
454 (Gate Protected)
455 (Gate Protected)

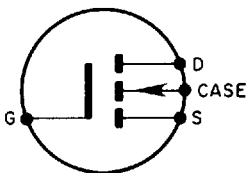
Enhancement N-Ch MOSFET



ECG

66 2382 2386 2390
67 2384 2387 2392
2380 2385 2388

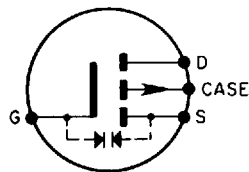
Enhancement N-Ch MOSFET



ECG

465

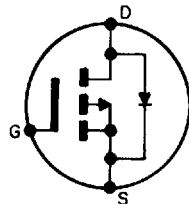
Enhancement P-Ch MOSFET



ECG

463 (Dual)
(Gate Protected)
464

Enhancement P-Ch MOSFET



ECG

2381
2382